ON Semiconductor

Is Now



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Configurable Dual Supply Octal Transceiver

with 3-State Outputs for 3 V Systems

The 74LVXC3245 is a 24-pin dual-supply, octal configurable voltage interface transceiver especially well suited for PCMCIA and other real time configurable I/O applications. The V_{CCA} pin accepts a 3.0 V supply level; the A port is a dedicated 3.0 V port. The V_{CCB} pin accepts a 3.0 V-to-5.0 V supply level. The B port is configured to track the V_{CCB} supply level. A 5.0 V level on the V_{CCB} pin will configure the I/O pins at a 5.0 V level and a 3.0 V V_{CCB} will configure the I/O pins at a 3.0 V level. The A port interfaces with a 3.0 V host system and the B port to the card slots. This device will allow the V_{CCB} voltage source pin and I/O pins on the B port to float when \overline{OE} is High. This feature is necessary to buffer data to and from a PCMCIA socket that permits PCMCIA cards to be inserted and removed during normal operation. The Transmit/Receive (T/\overline{R}) input determines the direction of data flow. Transmit (active-High) enables data from the A port to B port. Receive (active-Low) enables data from the B port to the A port.

Features

- Bidirectional Interface Between 3.0 V and 3.0 V/5.0 V Buses
- Control Inputs Compatible with TTL Level
- Outputs Source/Sink Up to 24 mA
- Guaranteed Simultaneous Switching Noise Level and Dynamic Threshold Performance
- Available in SOIC and TSSOP Packages
- Flexible V_{CCB} Operating Range
- Allows B Port and V_{CCB} to Float Simultaneously When \overline{OE} is High
- Functionally Compatible With the 74 Series 245
- These Devices are Pb-Free and are RoHS Compliant



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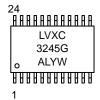
http://onsemi.com

MARKING DIAGRAMS









LVXC3245 = Specific Device Code A = Assembly Location

WL, L = Wafer Lot Y = Year WW, W = Work Week G = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

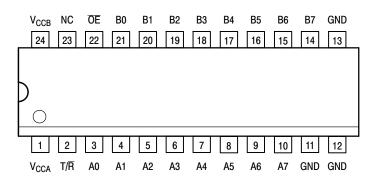


Figure 1. 24-Lead Pinout (Top View)

PIN NAMES

Pins	Function
OE	Output Enable Input
T/R	Transmit/Receive Input
A0-A7	Side A 3–State Inputs or 3–State Outputs
B0-B7	Side B 3–State Inputs or 3–State Outputs

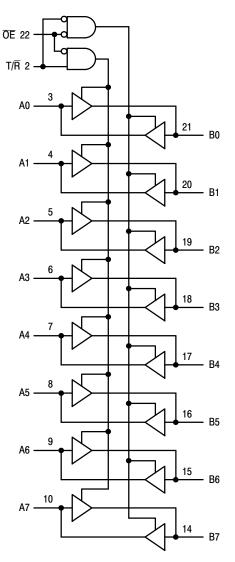


Figure 2. Logic Diagram

INP	UTS	OPERATING MODE
ŌĒ	T/R	Non-Inverting
L	L	B Data to A Bus
L	Н	A Data to B Bus
Н	Х	Z

H = High Voltage Level; L = Low Voltage Level; Z = High Impedance State; X = High or Low Voltage Level and Transitions are Acceptable; for I_{CC} reasons, Do Not Float Inputs

MAXIMUM RATINGS

Symbol	Parameter		Value	Condition	Unit
V _{CCA} , V _{CCB}	DC Supply Voltage		-0.5 to +7.0		V
VI	DC Input Voltage	ŌĒ, T/R	-0.5 to V _{CCA} +0.5		V
V _{I/O}	DC Input/Output Voltage	An	-0.5 to V _{CCA} +0.5		V
		Bn	-0.5 to V _{CCB} +0.5		V
I _{IK}	DC Input Diode Current	OE, T/R	±20	V _I < GND	mA
I _{OK}	DC Output Diode Current		±50	$V_O < GND; V_O > V_{CC}$	mA
I _O	DC Output Source/Sink Current		±50		mA
I _{CC} , I _{GND}	DC Supply Current	Per Output Pin Maximum Current	±50 ±200		mA
T _{STG}	Storage Temperature Range		-65 to +150		°C
	DC Latchup Source/Sink Current		±300		mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

RECOMMENDED OPERATING CONDITIONS

Symbol	Para	Min	Max	Unit	
V _{CCA} , V _{CCB}	Supply Voltage (V _{CCA} ≤ V _{CCB})	V _{CCA} V _{CCB}	2.3 3.0	3.6 5.5	V
VI	Input Voltage	ŌĒ, T/R	0	V_{CCA}	V
V _{I/O}	Input/Output Voltage	An Bn	0	V _{CCA} V _{CCB}	V
T _A	Operating Free–Air Temperature	-40	+85	°C	
Δt/ΔV	Minimum Input Edge Rate V $_{\rm IN}$ from 30% to 70% of V $_{\rm CC}$; V $_{\rm CC}$ at 3.0 V, 4.5 V, 5.5 V			8	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

						T _A =	25°C	T _A = -40 to +85°C	
Symbol	Parameter		Condition	V _{CCA}	V _{CCB}	Тур	Gı	uaranteed Limits	Unit
V _{IHA}	Minimum HIGH Level Input Voltage	An OE T/R	V _{OUT} ≤ 0.1 V	2.3 3.0 3.6	3.0 3.6 5.5		2.0 2.0 2.0	2.0 2.0 2.0	V
V _{IHB}		Bn	or ≥ V _{CC} – 0.1 V	2.3 3.0 3.6	3.0 3.6 5.5		2.00 2.00 3.85	2.00 2.00 3.85	V
V _{ILA}	Maximum LOW Level Input Voltage	An OE T/R	V _{OUT} ≤ 0.1 V	2.3 3.0 3.6	3.0 3.6 5.5		0.8 0.8 0.8	0.8 0.8 0.8	V
V _{ILB}		Bn	or ≥ V _{CC} – 0.1 V	2.3 3.0 3.6	3.0 3.6 5.5		0.80 0.80 1.65	0.80 0.80 1.65	V
V _{OHA}	Minimum HIGH Level Output Voltage		$I_{OUT} = -100 \mu A$ $I_{OH} = -12 mA$ $I_{OH} = -24 mA$ $I_{OH} = -12 mA$ $I_{OH} = -24 mA$	3.0 3.0 3.0 2.3 2.3	3.0 3.0 3.0 3.0 4.5	2.99 2.85 2.65 2.50 2.30	2.90 2.56 2.35 2.30 2.10	2.90 2.46 2.25 2.20 2.00	V
V _{OHB}			$I_{OUT} = -100 \mu A$ $I_{OH} = -12 \text{ mA}$ $I_{OH} = -24 \text{ mA}$ $I_{OH} = -24 \text{ mA}$	3.0 3.0 3.0 3.0	3.0 3.0 3.0 4.5	2.99 2.85 2.65 4.25	2.90 2.56 2.35 3.86	2.90 2.46 2.25 3.76	V

DC ELECTRICAL CHARACTERISTICS

						T _A =	25°C	T _A = -40 to +85°C	
Symbol	Parameter		Condition	V _{CCA}	V _{CCB}	Тур	Gı	uaranteed Limits	Unit
V _{OLA}	Maximum LOW Level Output Voltage		I _{OUT} = 100 μA I _{OL} = 24 mA I _{OL} = 12 mA I _{OL} = 24 mA	3.0 3.0 2.7 2.7	3.0 3.0 3.0 4.5	0.002 0.21 0.11 0.22	0.10 0.36 0.36 0.42	0.10 0.44 0.44 0.50	V
V _{OLB}			I_{OUT} = 100 μ A I_{OL} = 24 mA I_{OL} = 24 mA	3.0 3.0 3.0	3.0 3.0 4.5	0.002 0.21 0.18	0.10 0.36 0.36	0.10 0.44 0.44	V
I _{IN}	Max Input Leakage Current	OE, T/R	$V_I = V_{CCA}$, GND	3.6 3.6	3.6 5.5		±0.1 ±0.1	±1.0 ±1.0	μΑ
I _{OZA}	Max 3-State Output Leakage	An	$\begin{aligned} & V_{I} = V_{IH}, \ V_{IL} \\ & \overline{OE} = V_{CCA} \\ & V_{O} = V_{CCA}, \ GND \end{aligned}$	3.6 3.6	3.6 5.5		±0.5 ±0.5	±5.0 ±5.0	μΑ
I _{OZB}	Max 3-State Output Leakage	Bn	$\begin{aligned} & V_{I} = V_{IH}, V_{IL} \\ & \overline{OE} = V_{CCA} \\ & V_{O} = V_{CCB}, GND \end{aligned}$	3.6 3.6	3.6 5.5		±0.5 ±0.5	±5.0 ±5.0	μΑ
ΔI_{CC}	Maximum I _{CC} /Input	Bn	$V_I = V_{CCB} - 2.1 \text{ V}$	3.6	5.5	1.0	1.35	1.5	mA
		All In- puts	$V_{I} = V_{CC} - 0.6 \text{ V}$	3.6	3.6		0.35	0.5	mA
I _{CCA1}	Quiescent V _{CCA} Supply Current as B Port Floats		$\begin{aligned} &\text{An = V}_{\text{CCA}} \text{ or GND} \\ &\text{Bn = Open,} \\ &\overline{\text{OE}} = \text{V}_{\text{CCA}}, \\ &\text{T/R} = \text{V}_{\text{CCA}}, \\ &\text{V}_{\text{CCB}} = \text{Open} \end{aligned}$	3.6	Open		5	50	μΑ
I _{CCA2}	Quiescent V _{CCA} Supply Current		$\begin{array}{c} \text{An} = \text{V}_{\text{CCA}} \text{ or GND} \\ \text{Bn} = \text{V}_{\text{CCB}} \text{ or} \\ \text{GND, } \overline{\text{OE}} = \text{GND,} \\ \overline{\text{T/R}} = \text{GND} \end{array}$	3.6 3.6	3.6 5.5		5 5	50 50	μΑ
I _{CCB}	Quiescent V _{CCB} Supply Current		$\begin{aligned} &An = V_{CCA} \text{ or } GND \\ &Bn = V_{CCB} \text{ or} \\ &GND, \ \overline{OE} = GND, \\ &T/R = V_{CCA} \end{aligned}$	3.6 3.6	3.6 5.5		5 8	50 80	μΑ
V _{OLPA}	Quiet Output Max Dy- namic V _{OL}		Notes 1, 2	3.3 3.3	3.3 5.0		0.8 0.8		V
V _{OLPB}			Notes 1, 2	3.3 3.3	3.3 5.0		0.8 1.5		V
V _{OLVA}	Quiet Output Min Dy- namic V _{OL}		Notes 1, 2	3.3 3.3	3.3 5.0		-0.8 -0.8		V
V _{OLVB}			Notes 1, 2	3.3 3.3	3.3 5.0		-0.8 -1.2		V
V _{IHDA}	Min HIGH Level Dy- namic Input Voltage		Notes 1, 3	3.3 3.3	3.3 5.0		2.0 2.0		V
V _{IHDB}			Notes 1, 3	3.3 3.3	3.3 5.0		2.0 3.5		V
V _{ILDA}	Max LOW Level Dy- namic Input Voltage		Notes 1, 3	3.3 3.3	3.3 5.0		0.8 0.8		V
V _{ILDB}			Notes 1, 3	3.3 3.3	3.3 5.0		0.8 1.5		V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product

performance may not be indicated by the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Worst case package.

2. Max number of outputs defined as (n). Data inputs are driven 0 V to V_{CC} level; one output at GND.

3. Max number of data inputs (n) switching. (n–1) inputs switching 0 V to V_{CC} level. Input under test switching: V_{CC} level to threshold (V_{ILD}), 0 V to threshold (V_{ILD}), f = 1 MHz.

AC ELECTRICAL CHARACTERISTICS

		$T_A = -40 \text{ to } +85^{\circ}\text{C}; C_L = 50 \text{ pF}$						
			_{CCA} = 2.7-3.0 _{CCB} = 4.5-5.0			_{CA} = 2.7-3.0 _{CB} = 3.0-3.0		
Symbol	Parameter	Min	Typ (Note 4)	Max	Min	Typ (Note 5)	Max	Unit
t _{PHL} t _{PLH}	Propagation Delay A to B	1.0 1.0	4.8 3.9	8.5 7.0	1.0 1.0	5.5 5.2	9.0 8.5	ns
t _{PHL} t _{PLH}	Propagation Delay B to A	1.0 1.0	3.8 4.3	7.0 8.0	1.0 1.0	4.4 5.1	7.5 8.0	ns
t _{PZL}	Output Enable Time OE to B	1.0 1.0	4.7 4.8	8.5 9.0	1.0 1.0	6.0 6.1	9.5 10.0	ns
t _{PZL} t _{PZH}	Output Enable Time OE to A	1.0 1.0	5.9 5.4	10.0 9.5	1.0 1.0	6.4 5.8	10.5 9.5	ns
t _{PHZ}	Output Disable Time OE to B	1.0 1.0	4.0 3.8	8.5 8.0	1.0 1.0	6.3 4.5	10.0 8.5	ns
t _{PHZ}	Output Disable Time OE to A	1.0 1.0	4.6 3.1	10.0 7.0	1.0 1.0	5.2 3.4	10.0 7.0	ns
t _{OSHL} t _{OSLH}	Output to Output Skew, Data to Output (Note 6)		1.0	1.5		1.0	1.5	ns

CAPACITIVE CHARACTERISTICS

Symbol	Parameter		Condition		Unit
C _{IN}	Input Capacitance		$V_{CCA} = 3.3 \text{ V}; V_{CCB} = 5.0 \text{ V}$	4.5	pF
C _{I/O}	Input/Output Capacitance		$V_{CCA} = 3.3 \text{ V}; V_{CCB} = 5.0 \text{ V}$	10	pF
C _{PD}	Power Dissipation Capacitance (Measured at 10 MHz)	A→B B→A	$V_{CCB} = 5.0 \text{ V}$ $V_{CCA} = 3.3 \text{ V}$	50 40	pF

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74LVXC3245DWRG	SOIC-24 (Pb-Free)	1000 Tape & Reel
MC74LVXC3245DTG	TSSOP-24* (Pb-Free)	62 Units / Rail
MC74LVXC3245DTR2G	TSSOP-24* (Pb-Free)	2500 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Typical values at V_{CCA} = 3.3 V, V_{CCB} = 5.0 V at 25°C.
 Typical values at V_{CCA} = 3.3 V, V_{CCB} = 3.3 V at 25°C.
 Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.

^{*}This package is inherently Pb-Free.

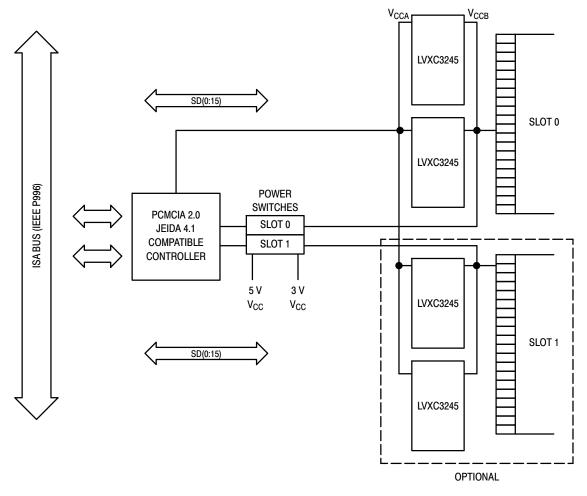


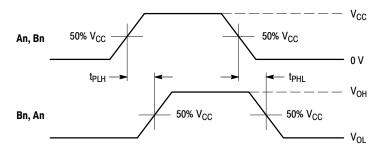
Figure 3. Block Diagram

Configurable I/O Application for PCMCIA Cards

The 74LVXC3245 is a dual–supply device well suited for PCMCIA configurable I/O applications. The LVXC3245 consumes less than 1mW of quiescent power in all modes of operation, making it ideal for low power notebook designs. The LVXC3245 meets all PCMCIA I/O voltage requirements at 5.0 V and 3.3 V operation. By tying the $V_{\rm CCB}$ pin to the card voltage supply, the PCMCIA card will always have

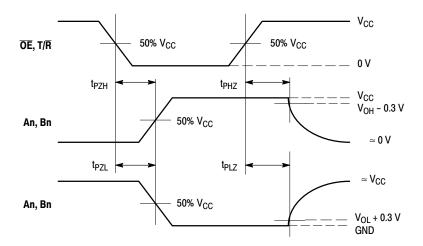
rail-to-rail output swings, maximizing the reliability of the interface.

The V_{CCA} pin must always be tied to a 3.3 V power supply. This voltage connection provides internal references needed to account for variations in V_{CCB} . When connected as in the figure above, the LVXC3245 meets all the voltage and current requirements of the ISA bus standard (IEEE P996).



WAVEFORM 1 - PROPAGATION DELAYS

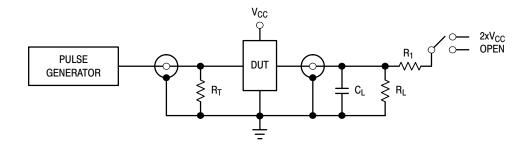
 t_R = t_F = 2.5 ns, 10% to 90%; f = 1 MHz; t_W = 500 ns



WAVEFORM 2 - OUTPUT ENABLE AND DISABLE TIMES

 $t_R = t_F = 2.5 \text{ ns}, 10\% \text{ to } 90\%; f = 1 \text{ MHz}; t_W = 500 \text{ ns}$

Figure 4. AC Waveforms



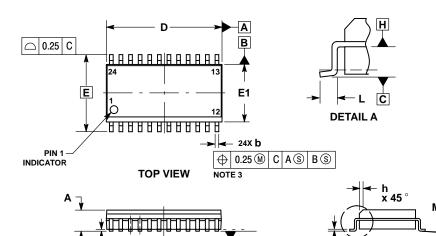
TEST	SWITCH
t _{PLH} , t _{PHL} , t _{PZH} , t _{PHZ}	Open
t _{PZL} , t _{PLZ}	2xV _{CC}

 C_L = 50 pF or equivalent (Includes jig and probe capacitance) R_L = R_1 = 500 Ω or equivalent R_T = Z_{OUT} of pulse generator (typically 50 Ω)

Figure 5. Test Circuit

PACKAGE DIMENSIONS

SOIC-24 **DW SUFFIX** CASE 751E-04 ISSUE F



е

SIDE VIEW

NOTE 5

C SEATING PLANE

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

 2. CONTROLLING DIMENSION: MILLIMETERS.

 3. DIMENSIONS 6 AND c APPLY TO THE FLAT SECTION OF THE LEAD AND ARE MEASURED BETWEEN 0.10 AND 0.25 FROM THE LEAD TIP.

 4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR PROTRUSION SIDE. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 PER SIDE. DIMENSIONS D AND E1 ARE DETERMINED AT DATUM H.

 5. A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.

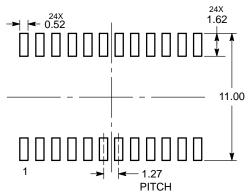
	MILLIMETERS					
DIM	MIN	MAX				
Α	2.35	2.65				
A1	0.13	0.29				
b	0.35	0.49				
С	0.23	0.32				
D	15.25	15.54				
Е	10.30	BSC				
E1	7.40	7.60				
е	1.27 BSC					
h	0.25	0.75				
L	0.41	0.90				
M	0 °	8 °				

RECOMMENDED SOLDERING FOOTPRINT*

DFTAIL A

END VIEW

NOTE 3



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.